Revised January 1999

FAIRCHILD

SEMICONDUCTOR

CD4007C **Dual Complementary Pair Plus Inverter**

General Description

The CD4007C consists of three complementary pairs of Nand P-channel enhancement mode MOS transistors suitable for series/shunt applications. All inputs are protected from static discharge by diode clamps to V_{DD} and $V_{\text{SS}}.$

For proper operation the voltages at all pins must be constrained to be between V_{SS} – 0.3V and V_{DD} + 0.3V at all times.

October 1987

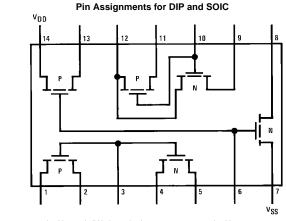
Features

- Wide supply voltage range: 3.0V to 15V
- High noise immunity: 0.45 V_{CC} (typ.)

Ordering Code:

Order Number	Package Number	Package Description				
CD4007CM	M14A	14-Lead Small Outline Integrated Circuit (SOIC), JEDEC MS-120, 0.150" Narrow				
CD4007CN	N14A	14-Lead Plastic Dual-In-Line Package (PDIP), JEDEC MS-001, 0.300" Wide				
Devices also available in Tape and Reel. Specify by appending the suffix letter "X" to the ordering code.						

Connection Diagram



Note: All P-channel substrates are connected to $\rm V_{DD}$ and all N-channel substrates are connected to $\rm V_{SS}.$

Top View

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Absolute Maximum Ratings(Note 1)

		V_{SS} –0.3V to V_{DD} +0.3V	Voltage at Any Pin
Power Dissipation (P _D) Dual-In-Line 700 mW		-40°C to +85°C	Operating Temperature Range
Dual-In-Line 700 mW	L	-65°C to +150°C	Storage Temperature Range
N			Power Dissipation (P _D)
	No	700 mW	Dual-In-Line
	be	500 mW	Small Outline

Operating V_{DD} Range Lead Temperature (Soldering, 10 seconds) V_{SS} +3.0V to V_{SS} +15V

260°C

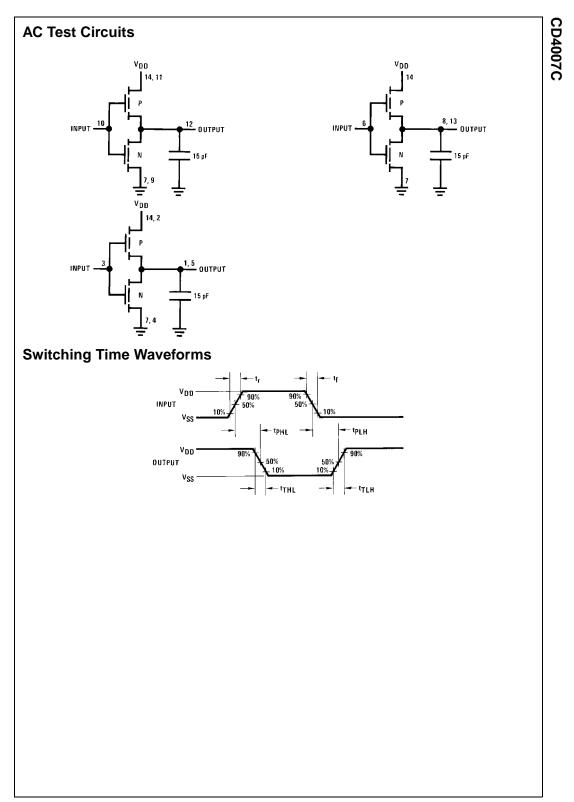
Note 1: This device should not be connected to circuits with the power on because high transient voltages may cause permanent damage.

DC Electrical Characteristics

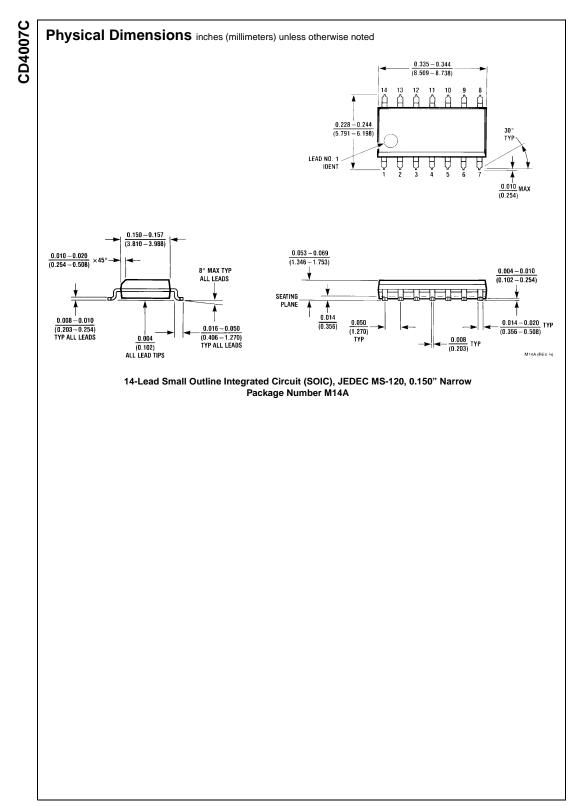
	Parameter		Limits									
Symbol		Conditions	-40°C		+25°C			+85°C			Units	
			Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	
և	Quiescent Device	$V_{DD} = 5.0V$			0.5		0.005	0.05			15	μA
	Current	$V_{DD} = 10V$			1.0		0.005	1.0			30	μΑ
PD	Quiescent Device	$V_{DD} = 5.0V$			2.5		0.025	2.5			75	μW
	Dissipation Package	$V_{DD} = 10V$			10		0.05	10			300	μW
V _{OL}	Output Voltage	$V_{DD} = 5.0V$			0.05		0	0.01			0.05	V
	LOW Level	$V_{DD} = 10V$			0.05		0	0.01			0.05	V
V _{OH}	Output Voltage	$V_{DD} = 5.0V$	4.95			4.95	5.0		4.95			V
	HIGH Level	$V_{DD} = 10V$	9.95			9.95	10		9.95			V
V _{NL}	Noise Immunity	$V_{DD} = 5.0V, V_{O} = 3.6V$			1.5		2.25	1.5			1.4	V
	(All inputs)	$V_{DD} = 10V, V_{O} = 7.2V$			3.0		4.5	3.0			2.9	V
V _{NH}	Noise Immunity	$V_{DD} = 5.0V, V_{O} = 0.95V$	3.6			3.5	2.25		3.5			V
	(All Inputs)	$V_{DD} = 10V, V_{O} = 2.9V$	7.1			7.0	4.5		7.0			V
I _D N	Output Drive Current	$V_{DD} = 5.0V, V_{O} = 0.4V, V_{I} = V_{DD}$	0.35			0.3	1.0		0.24			mA
	N-Channel	$V_{DD} = 10V, V_{O} = 0.5V, V_{I} = V_{DD}$	1.2			1.0	2.5		0.8			mA
I _D P	Output Drive Current	$V_{DD} = 5.0V, V_{O} = 2.5V, V_{I} = V_{SS}$	-1.3			-1.1	-4.0		-0.9			mA
	P-Channel	$V_{DD} = 10V, V_{O} = 9.5V, V_{I} = V_{SS}$	-0.65			-0.55	-2.5		-0.45			mA
l _l	Input Current						10					pА

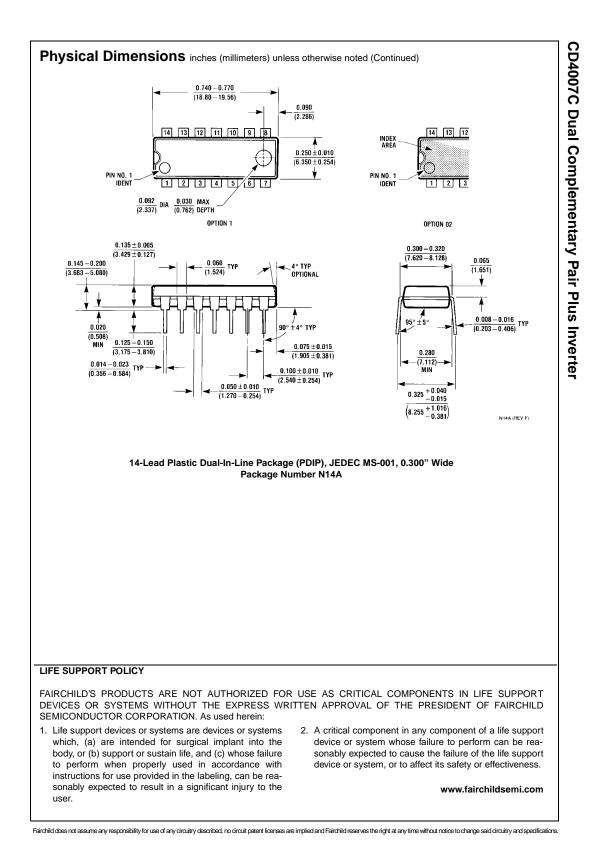
AC Electrical Characteristics (Note 2) $T_A = 25^{\circ}C$ and $C_L = 15 \text{ pF}$ and rise and fall times = 20 ns. Typical temperature coefficient for all values of $V_{DD} = 0.3\%/^{\circ}C$

Symbol	Parameter	Conditions	Min	Тур	Max	Units	
$t_{PLH} = t_{PHL}$	Propagation Delay Time	V _{DD} = 5.0V		35	75	ns	
		$V_{DD} = 10V$		20	50	ns	
$t_{TLH} = t_{THL}$	Transition Time	$V_{DD} = 5.0V$		50	100	ns	
		$V_{DD} = 10V$		30	50	ns	
Cl	Input Capacitance	Any Input		5		pF	
Note 2: AC Parameters are guaranteed by DC correlated testing.							



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